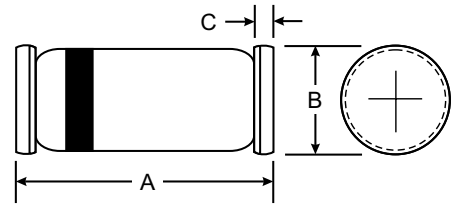


### Features

- Silicon Epitaxial Planar Diodes

### Mechanical Data

- Case: SOD-80/LL34, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)



LL34/ SOD-80		
Dim	Min	Max
<b>A</b>	3.30	3.70
<b>B</b>	1.30	1.60
<b>C</b>	0.28	0.50
All Dimensions in mm		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RRM}$	60	V
BAV200		120	
BAV201		200	
BAV203		250	
Reverse Voltage	$V_R$	50	V
BAV200		100	
BAV201		150	
BAV203		200	
Forward Current	$I_F$	250	mA
Forward Peak Current (at $f = 50$ Hz)	$I_{FM}$	625	mA
Peak Forward Surge Current (at $t_p = 1$ s)	$I_{FSM}$	1	A
Junction Temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_s$	- 65 to + 175	$^\circ\text{C}$

### Maximum Thermal Resistance at $T_j = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient at on PC board 50 mm X 50 mm X 1.6 mm	$R_{thJA}$	500	K/W

**Characteristics at  $T_a = 25^\circ\text{C}$** 

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	-	-	1	V
Reverse Current at $V_R = 50\text{ V}$ at $V_R = 100\text{ V}$ at $V_R = 150\text{ V}$ at $V_R = 200\text{ V}$	$I_R$	-	-	100	nA
	BAV200	-	-	100	nA
	BAV201	-	-	100	nA
	BAV202	-	-	100	nA
	BAV203	-	-	100	nA
Breakdown Voltage at $I_R = 100\ \mu\text{A}$	$V_{(BR)}$	60	-	-	V
	BAV200	120	-	-	V
	BAV201	200	-	-	V
	BAV202	250	-	-	V
	BAV203	-	-	-	V
Differential Forward Resistance at $I_F = 10\text{ mA}$	$r_f$	-	5	-	$\Omega$
Capacitance at $V_R = 0, f = 1\text{ MHz}$	$C_D$	-	1.5	-	pF
Reverse Recovery Time at $I_F = 30\text{ mA}, I_R = 30\text{ mA}, I_R = 3\text{ mA}, R_L = 100\ \Omega$	$t_{rr}$	-	-	50	ns

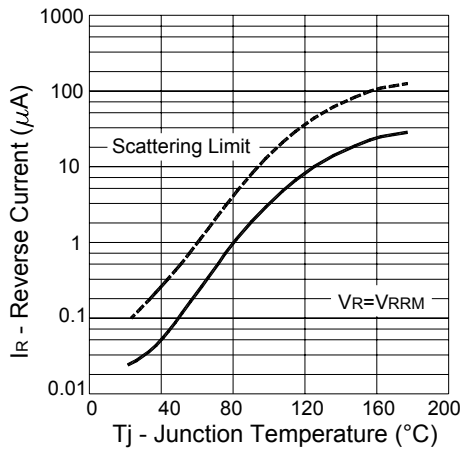
**Characteristics ( $T_j = 25^\circ\text{C}$  unless otherwise specified)**


Fig 1. Reverse Current vs. Junction Temperature

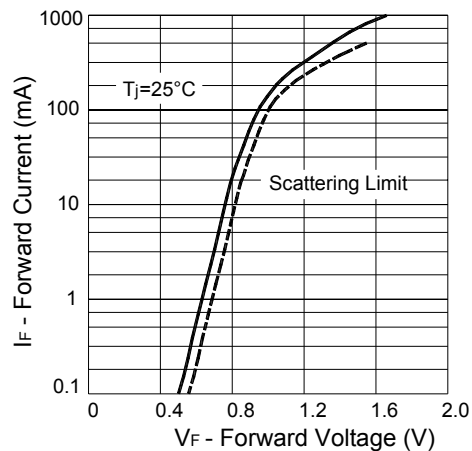


Fig 2. Forward Current vs. Forward Voltage